

EAST - [resistor.wsp.1]

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Doc: USPAT 438/238

Development: [ ] or [ ]

8 and ((remov53 or clean53) near5 ((native or natural) adj oxide))

Active

- L1: (31689) (oxide adj (film51 or layer51)) c
- L2: (2505) 1 and ((native or natural) adj3 ox
- L3: (1186) 2 and (gate.clm. or electrode.clm.
- L4: (1045) 3 and (polysilicon or silicon or c
- L5: (959) 4 and (oxide near10 (mask or oxide)
- L6: (226) 5 and ((natural or native) adj2 oxi
- L7: (137) 6 and (mask or resist or photoresis
- L8: (68) 7 and ((mask or resist or photoresis
- L10: (42) 8 and ((remov53 or clean53) near5 (
- L9: (49) 8 and ((remov53 or clean53) near5 (

Failed

Saved

- (0) ("thinadjfilm)nearresistor").PN.
- (0) ("thinadjfilm)nearresistor").PN.
- (150130) thin adj film
- (14857) (thin adj film) and resistor
- (2054) ((thin adj film) and resistor) and ((t
- (1735) (((thin adj film) and resistor) and ((
- (801) (((thin adj film) and resistor) and ((

U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OF	Current XR	Retrieval	Inventor	S	C	J	Q
33				US 6165830	20001226	11	Method to decrease capacitance depletion.	438/238	257/E21.01		Lin, Dahcheng et al.				
34				US 6130132	20001010	20	Clean process for manufacturing of solit-	438/264	257/E21.20		Hsieh, Chia-Ta et al.				
35				US 6127221	20001003	10	In situ, one step, formation of selective	438/255	257/E21.01		Lin, Dahcheng et al.				
36				US 6096391	20000801	9	Method for improving electrical conductivity	427/580	427/255.4;		Muffoletto, Barry C. et al.				
37				US 6083815	20000704	13	Method of gate etching with thin gate oxide	438/585	257/E21.31		Tsai, Chia-Shiung et al.				
38				US 5998255	19991207	11	Method of fabricating DRAM capacitor	438/252	257/E21.64		Kung, Cheng-Chih et al.				
39				US 5940699	19990817	22	Process of fabricating semiconductor device	438/233	257/E21.16		Sumi, Hirofumi et al.				
40				US 5909625	19990601	6	Method for forming layer of hemispherical	438/398			Lim, Chan				
41				US 5899720	19990504	13	Process of fabricating salicide structure from	438/303	257/E21.16		Mikagi, Kaoru				
42				US 5877052	19990302	10	Resolution of hemispherical grained s	438/238	257/E21.01		Lin, Dahcheng et al.				
43				US 5851909	19981222	17	Method of producing semiconductor device us	438/567	257/E21.14		Kamiya, Masaaki et al.				
44				US 5821153	19981013	8	Method to reduce field	438/439	257/E21.55		Tsai, Chaochieh et al.				

33/34



**Expend**

Development (32) ☒ High biodiversity

品名 Name	ICP 浓度	检测时间	检测次数	检测结果
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